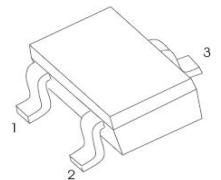


SOT-523 Plastic-Encapsulate Diodes

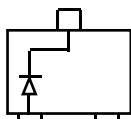
BAS70T/-04T/-05T/06T SCHOTTKY BARRIER DIODE

SOT-523

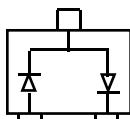


FEATURES

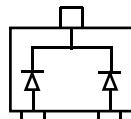
- Low Turn-on Voltage
- Fast Switching



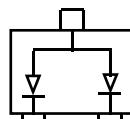
BAS70T Marking: 7C



BAS70-04T Marking: 7D



BAS70-05T Marking: 7E



BAS70-06T Marking: 7F

MARKING:

BAS70T	BAS70-04T	BAS70-05T	BAS70-06T
7C ?C	7D ?D	7E ?E	7F ?F

Maximum Ratings @Ta=25°C

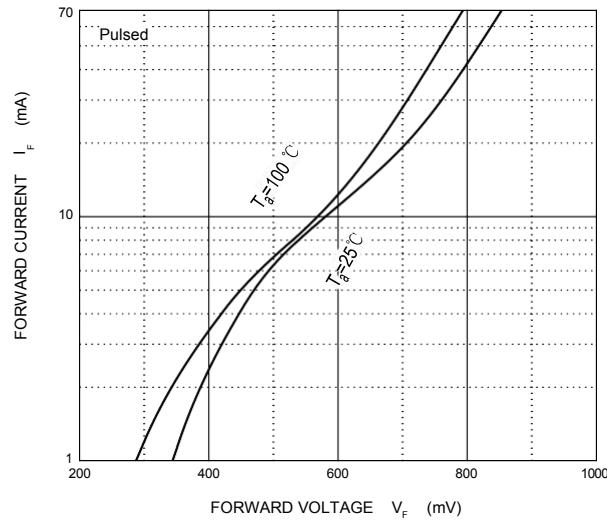
Parameter	Symbol	Limit	Unit
Peak Repetitive Peak Reverse Voltage	V _{RRM}		
Working Peak Reverse Voltage	V _{RWM}	70	V
DC Blocking Voltage	V _R		
Forward Continuous Current	I _{FM}	70	mA
Non-Repetitive Peak Forward Surge Current @ t = 8.3ms	I _{FSM}	100	mA
Power Dissipation	P _D	150	mW
Thermal Resistance Junction to Ambient	R _{θJA}	667	°C/W
Junction temperature	T _J	125	°C
Storage Temperature	T _{STG}	-55~+150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

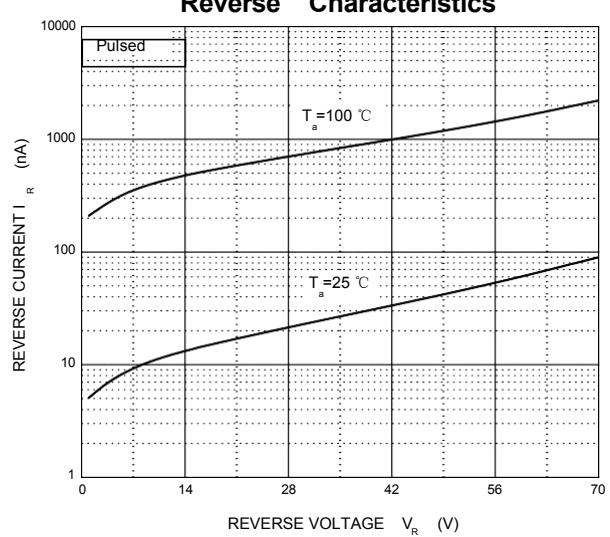
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	V _(BR)	I _R =10μA	70		V
Reverse voltage leakage current	I _R	V _R =50V		100	nA
Forward voltage	V _F	I _F =1mA I _F =15mA		410 1000	mV
Diode capacitance	C _D	V _R =0, f=1MHz		2	pF
Reveres recovery time	t _{rr}	I _F =I _R =10mA, I _{rr} =0.1xI _R , R _L =100Ω		5	ns

Typical Characteristics

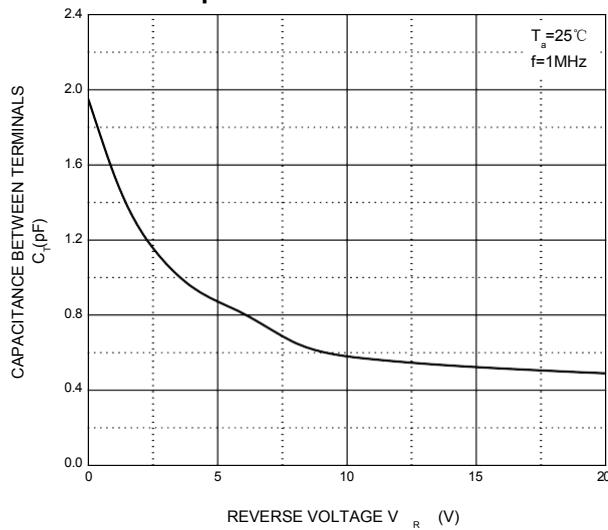
Forward Characteristics



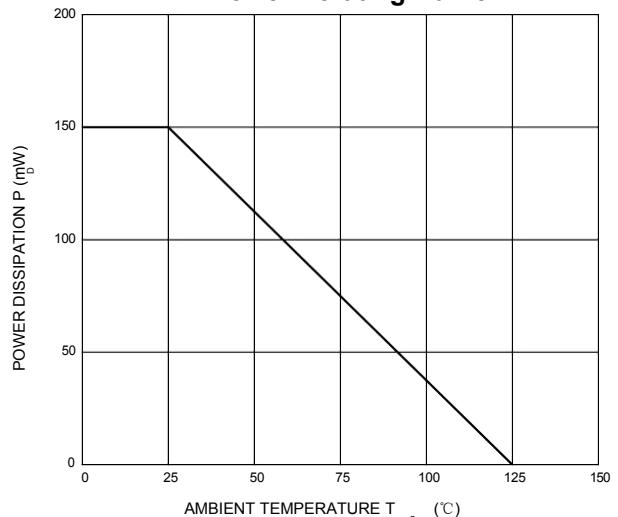
Reverse Characteristics



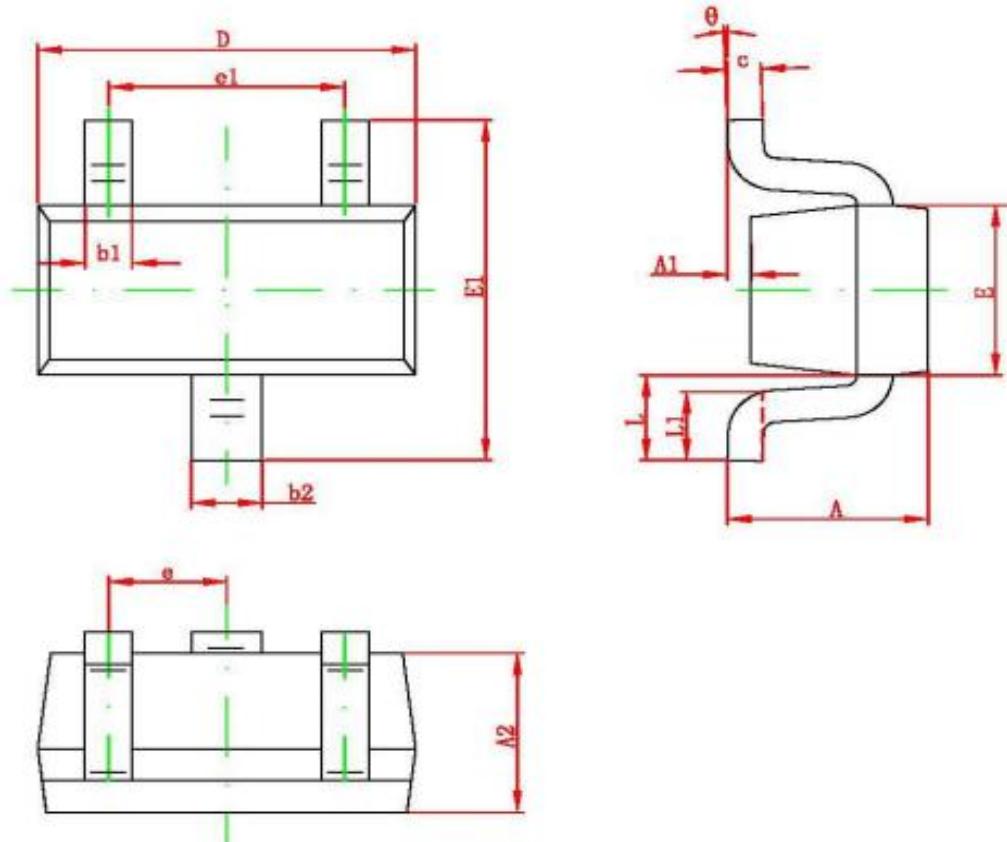
Capacitance Characteristics



Power Derating Curve



SOT-523 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500 TYP.		0.020 TYP.	
e1	0.900	1.100	0.035	0.043
L	0.400 REF.		0.016 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°